

isc Silicon NPN Power Transistor
KSH3055
DESCRIPTION

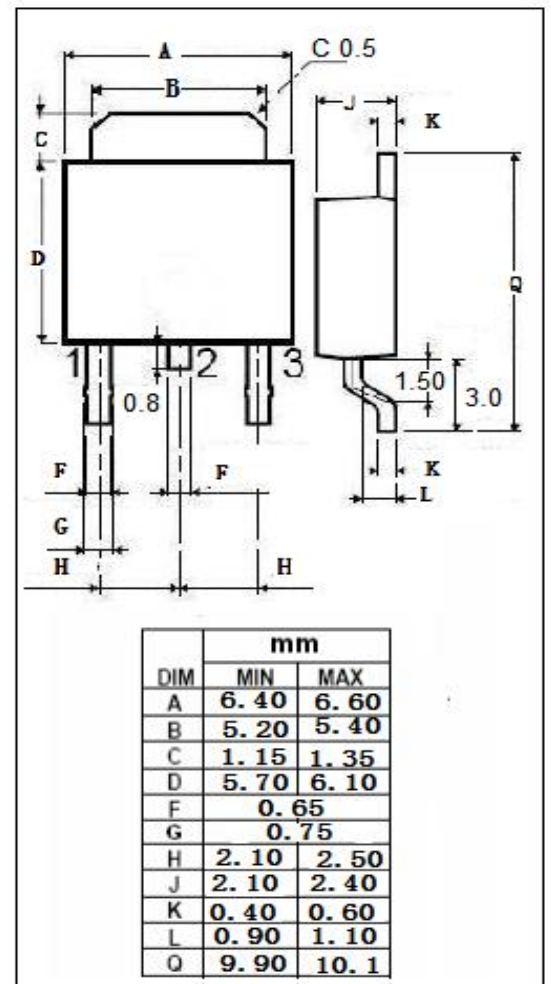
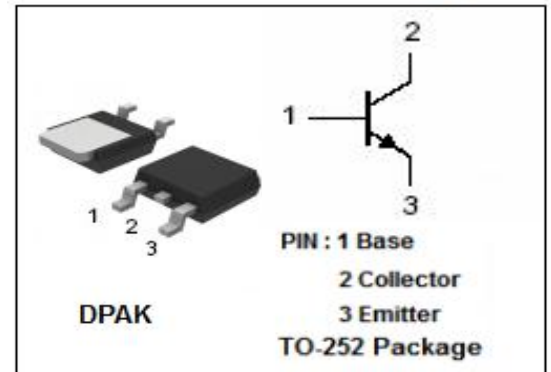
- High DC current gain
- Lead formed for surface mount applications(NO suffix)
- Straight lead(IPAK, “-I” suffix)
- DPAK for surface mount applications
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- General purpose amplifier low speed switching application

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|--------------------|
| V_{CBO} | Collector-Base Voltage | 70 | V |
| V_{CEO} | Collector-Emitter Voltage | 60 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 10 | A |
| I_B | Base Current-Continuous | 6 | A |
| P_C | Total Power Dissipation @ $T_a=25^{\circ}\text{C}$ | 1.75 | W |
| | Total Power Dissipation @ $T_c=25^{\circ}\text{C}$ | 20 | |
| T_J | Junction Temperature | 150 | $^{\circ}\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^{\circ}\text{C}$ |



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------------------|--------------------------------------|--|-----|-----|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 30mA; I _B = 0 | 60 | | | V |
| V _{CE(sat)-1*} | Collector-Emitter Saturation Voltage | I _C = 4A; I _B = 0.4A | | | 1.1 | V |
| V _{CE(sat)-2*} | Collector-Emitter Saturation Voltage | I _C = 10A; I _B = 3.3A | | | 8 | V |
| V _{BE(on)*} | Base-Emitter On Voltage | I _C = 4A; V _{CE} =4V | | | 1.8 | V |
| I _{CB0} | Collector Cutoff Current | V _{CB} = 70V; I _E = 0 | | | 2 | mA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 30V; I _B = 0 | | | 50 | uA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 0.5 | mA |
| h _{FE1*} | DC Current Gain | I _C = 4A; V _{CE} = 4V | 20 | | 100 | |
| h _{FE2*} | DC Current Gain | I _C = 10A; V _{CE} = 4V | 5 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = 0.5A; V _{CE} = 10V | 2 | | | MHz |

*:Pulse test PW≤300us,duty cycle≤2%

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